ABSTRACT OF THE DISCLOSURE

A highly-integrated, high speed semiconductor device includes a device isolation film defining an active region at a SOI wafer having a stacked structure of a first silicon layer, a filled insulating film and a second silicon layer—the second silicon layer being the active region between the device isolation film with an intervening first silicide layer; the first silicide layer formed on a gate electrode on the active region and an impurity junction region; and a second silicide layer intervening at the interface of a device isolation film and a second silicon layer and connected to the first silicide layer. Thus, operating characteristics of the device are improved by minimizing the resistance of an impurity junction region and reducing the manufacturing cost.

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